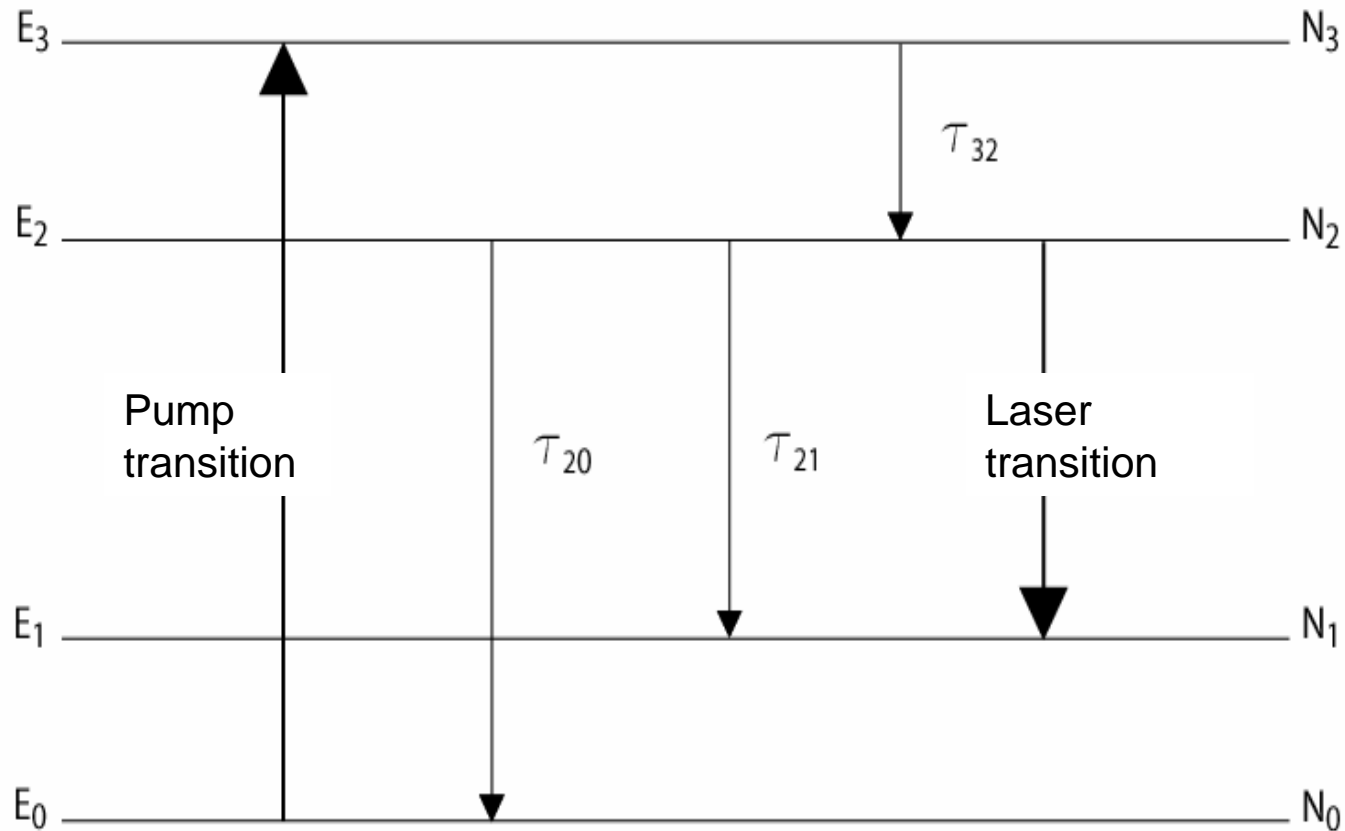


Computation of Laser Power Output



Energy levels, population numbers, and transitions for a 4-level laser system

Rate Equations for a 4-Level System

$$\frac{\partial N}{\partial t} = R_p - WN - \frac{N}{\tau}, \quad \frac{dS_L}{dt} = \iiint_a WN dV - \frac{S_L}{\tau_c}$$

$N(x,y,z) = N_2 - N_1$ population inversion density ($N_1 \sim 0$)

R_p pump rate

$W(x,y,z)$ transition rate due to stimulated emission

τ spontaneous fluorescence life time of upper laser level

S_L number of laser photons in the cavity

τ_c mean life time of laser photons in the cavity

The pump rate is given by

$$R_p = \eta_p S_p p_0$$

η_p pump efficiency

$p_0(x,y,z)$ absorbed pump power density distribution
normalized over the crystal volume

S_p total number of pump photons absorbed
in the crystal per time unit

The transition rate due to stimulated emission is given by

$$W = \frac{c\sigma}{n} S_L s_0(x, y, z)$$

σ stimulated emission cross section

n refractive index

$s_0(x,y,z)$ normalized energy density of the laser mode

Detailed Rate Equations of a 4-Level Systems

$$\frac{\partial N}{\partial t} = R_p - N \frac{c\sigma}{n} S_L s_0(x, y, z) - \frac{N}{\tau}$$

$$\frac{dS}{dt} = S_L \left[\iiint_a \frac{c\sigma}{n} N s_0(x, y, z) dV - \frac{1}{\tau_c} \right]$$

Condition for equilibrium

$$\partial N / \partial t = dS / dt = 0$$

Using the equilibrium conditions, and carrying through some transformations one is getting a recursion relation for the number of laser photons in the cavity

$$S_L = \tau_c \eta_p S_P \iiint_a \frac{p_0(x, y, z)}{1 + \frac{n}{c\sigma\tau S_L s_0(x, y, z)}} dV$$

This equation can be solved by iterative integration. The integral extends over the volume of the active medium. T is the transmission of the output coupler.

However, it is more convenient to derive an equation for the laser power output directly. Using the relations

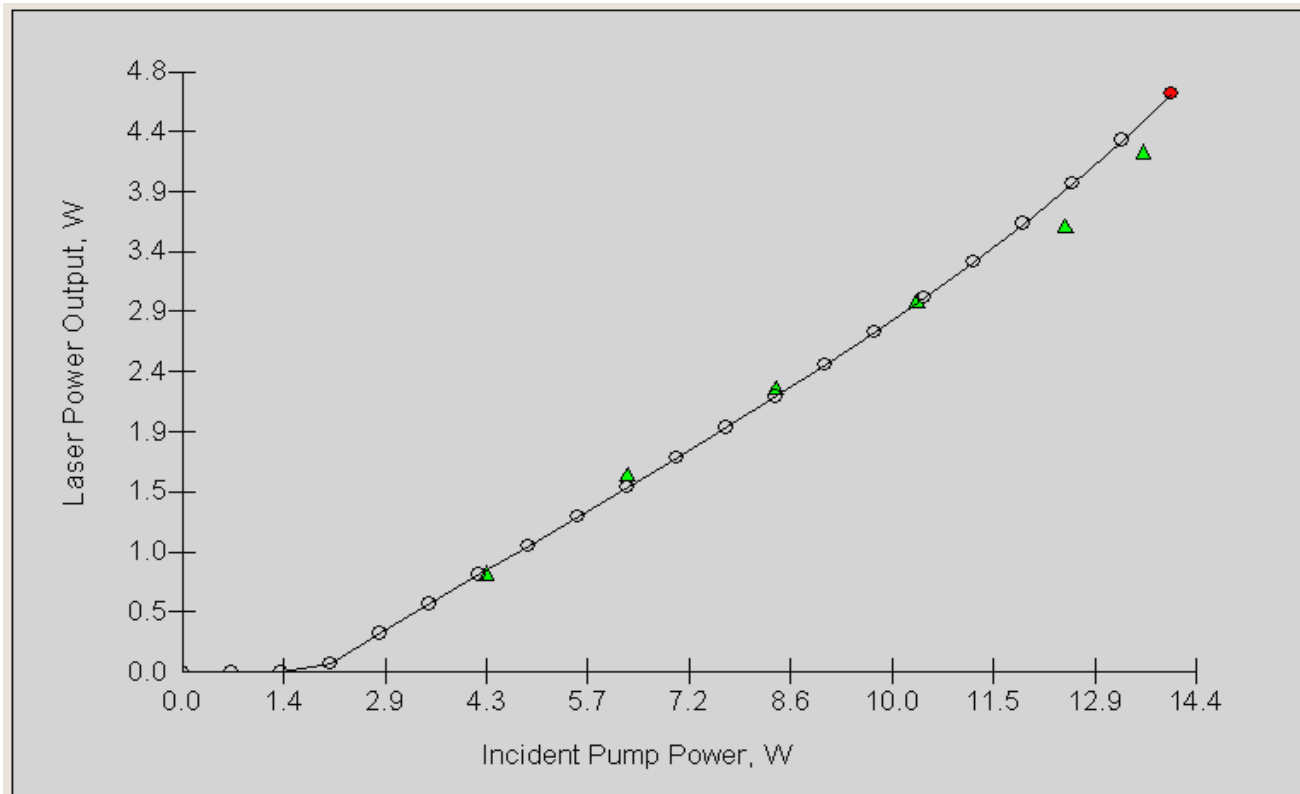
$$P_{out} = h\nu S_L \frac{c(-\ln(R_{out}))}{2\tilde{L}} \quad R_{out} \text{ Reflectivity of output mirror}$$

$$\tilde{L} = L_r + (n-1)L_a$$

$$T_T = L_{rountrip} - \ln(R_{out}) \quad \text{Total loss}$$

One obtains the recursion relation

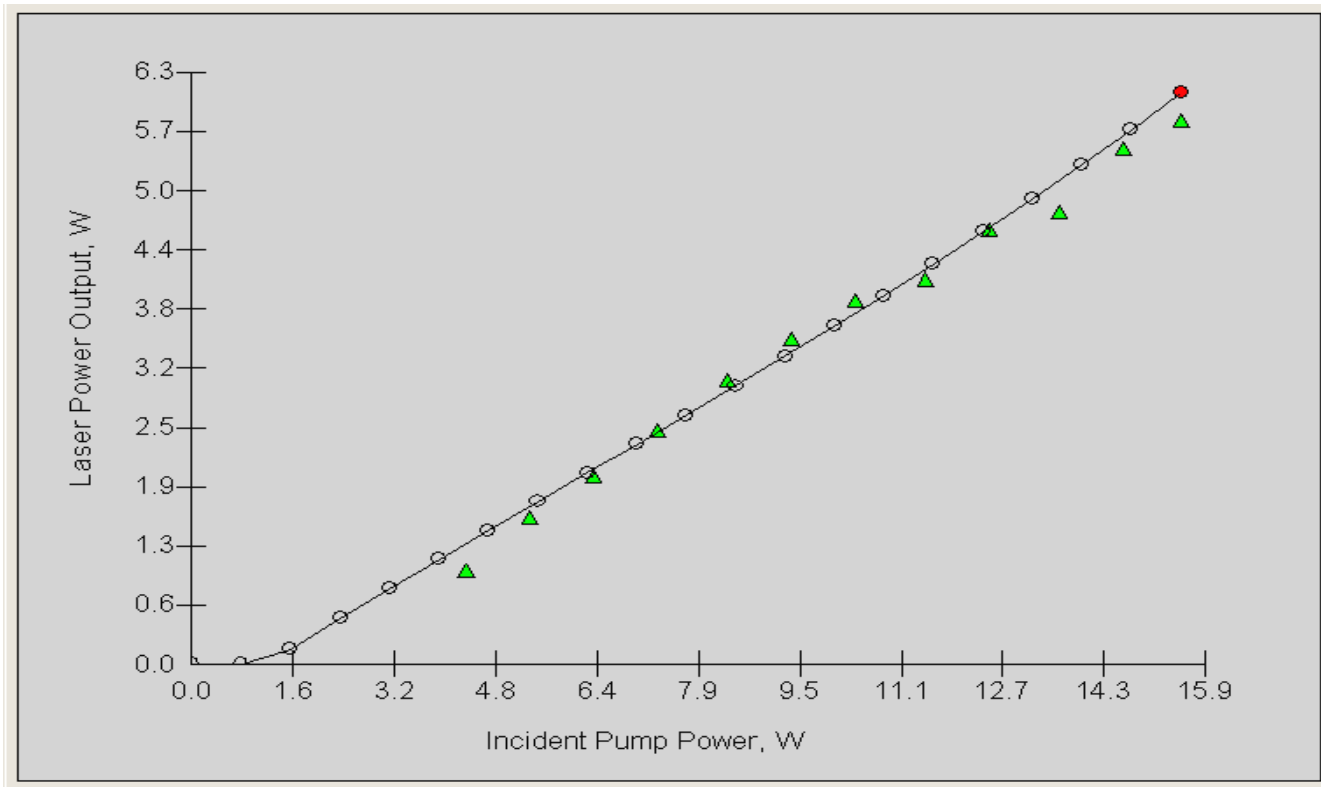
$$P_{out} = h\nu \frac{T_M}{T_T} \eta_p S_P \iiint_a \frac{P_0}{1 + \frac{nh\nu c T_M}{2P_{out} \tilde{L} s_0 c \sigma \tau}} dV$$



Example: Laser output power vs. pump power for 1.1 at. % Nd:YAG

▲ Measurement

o—o Computation

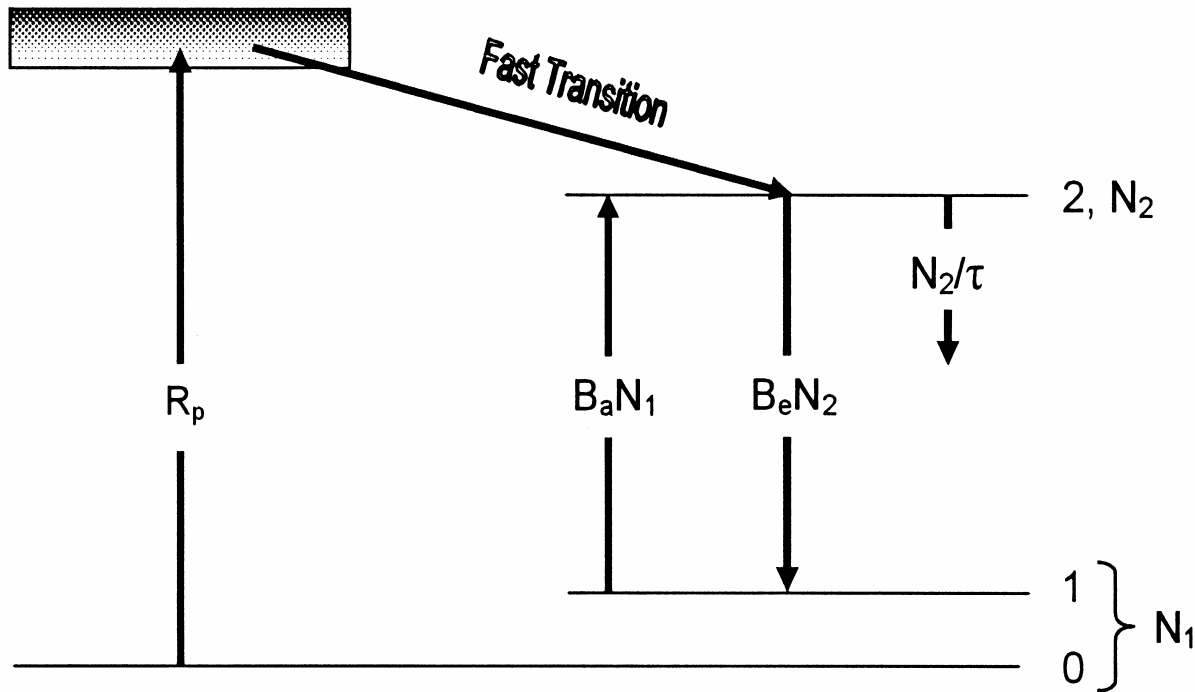


Example: Laser output power vs. pump power for 0.27 at. % Nd:YVO₄

▲ Measurement

o—o Computation

In similar way the laser power output for a quasi-3-level laser system can be computed



Energy levels, population numbers, and transitions for a quasi-3-level laser system

Rate Equations for a Quasi-3-Level System

$$N_t = N_1 + N_2$$

$$\frac{\partial N_2}{\partial t} = R_p - B_e N_2 + B_a N_1 - \frac{N_2}{\tau}$$

$$\frac{\partial S_L}{\partial t} = \iiint_a (B_e N_2 - B_a N_1) dV - \frac{S_L}{\tau_C}$$

N_t doping density per unit volume

B_e transition rate for stimulated emission

$$B_e = \frac{c \sigma_e}{n} S_L s_0(x, y, z)$$

B_a transition rate for reabsorption

$$B_a = \frac{c\sigma_a}{n} S_L s_0(x, y, z)$$

$\sigma_e(T(x, y, z))$ effective cross section of stimulated emission

σ_a effective cross section of reabsorption

c the vacuum speed of light

To solve the rate equation again equilibrium conditions are used

$$\partial N / \partial t = dS / dt = 0$$

After some transformations this recursion relation is obtained

$$P_{out} = \frac{h c T_M}{\lambda_L T_T} \iiint_a \frac{q_\sigma \eta_p \lambda_p P_p p_0 / (h c) - (q_\sigma - 1) N_t / \tau}{q_\sigma + \frac{h c T_M}{P_{out} (s_{GR} + s_{GL}) \sigma \tau \lambda_L}} dV$$

This recursion relation differs from the relation for 4-level-systems only due to the term

$$q_\sigma = 1 + \frac{\sigma_a}{\sigma_e}$$

$$\sigma_a \rightarrow 0 \quad \Rightarrow \quad q_\sigma \rightarrow 1$$

For $q_\sigma = 1$ the relation goes over into the relation for 4-level systems

The parameter q_σ depends on temperature distribution due to temperature dependence of the cross section σ_e of stimulated emission. σ_e can be computed by the use of the method of reciprocity. As shown in the paper of Laura L. DeLoach et al. , IEEE J. of Q. El. **29**, 1179 (1993) the following relation can be deduced

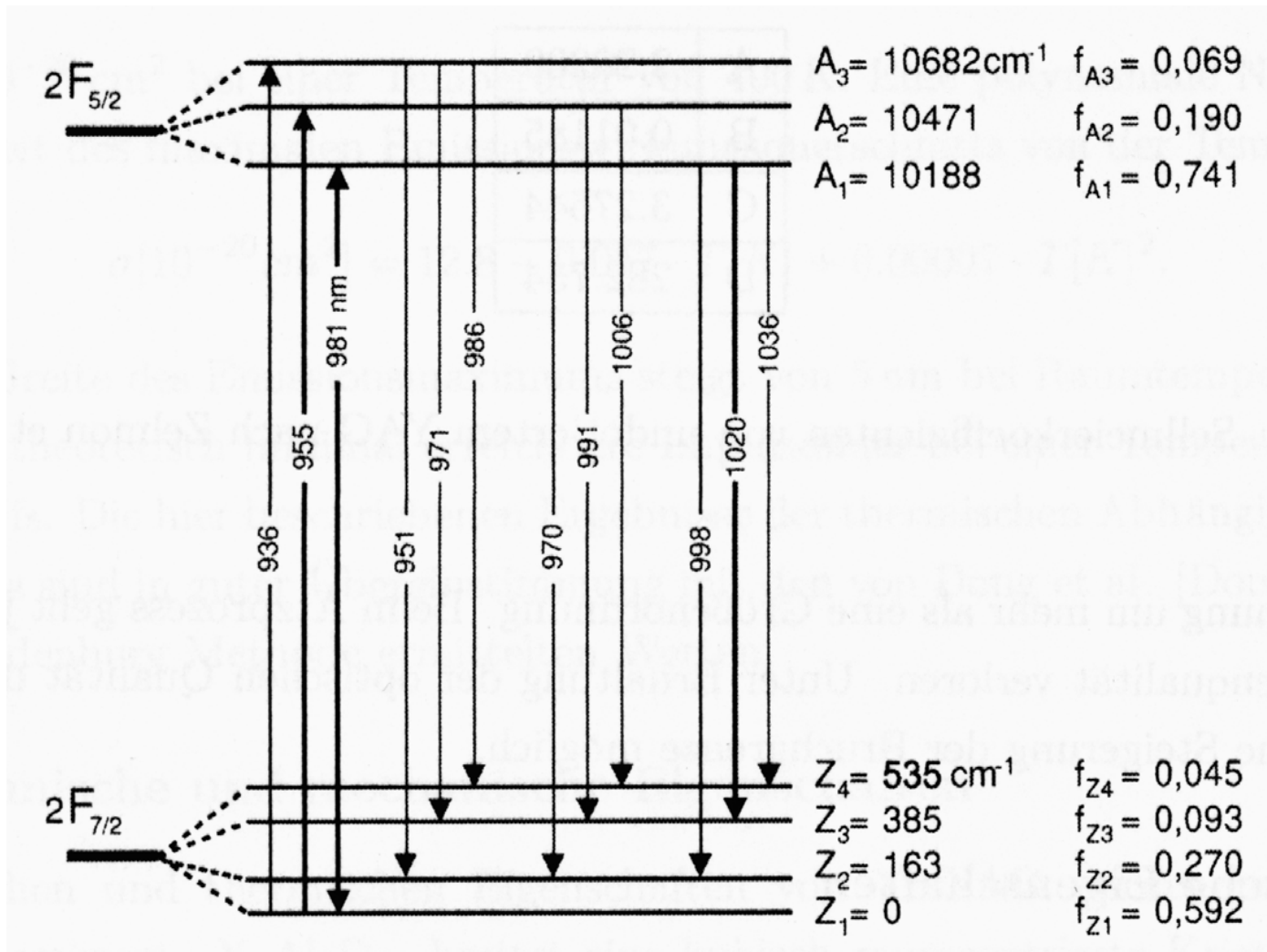
$$\sigma_e = \sigma_a \frac{Z_l(T(x, y, z))}{Z_u(T(x, y, z))} \exp\left(\frac{E_{zL} - h\nu}{kT(x, y, z)}\right)$$

Z_u and Z_l are the partition functions of the upper and lower crystal field states

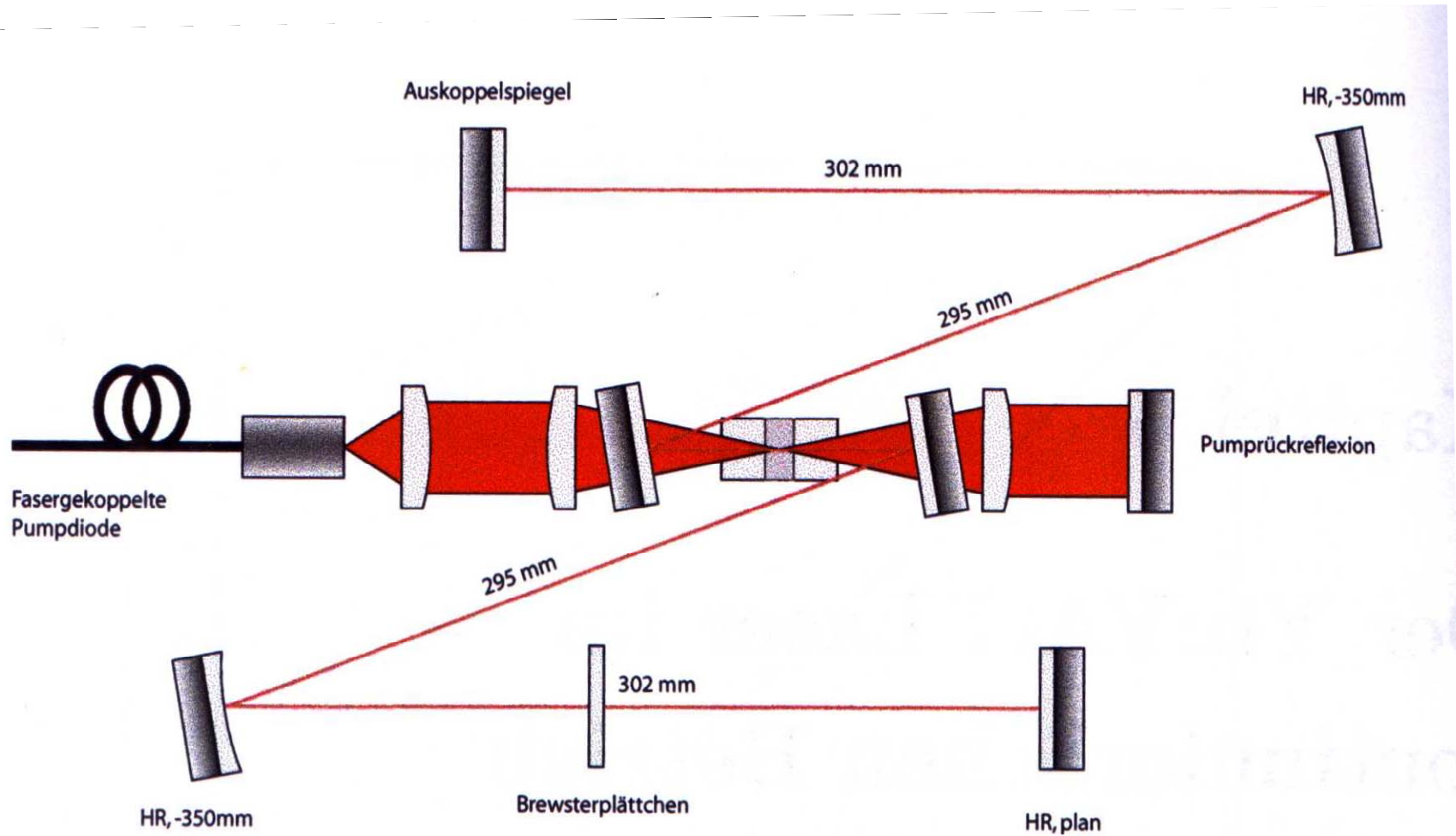
E_{zL} is the energy separation between lowest components of the upper and the lower crystal field states.

k is Boltzmann's constant

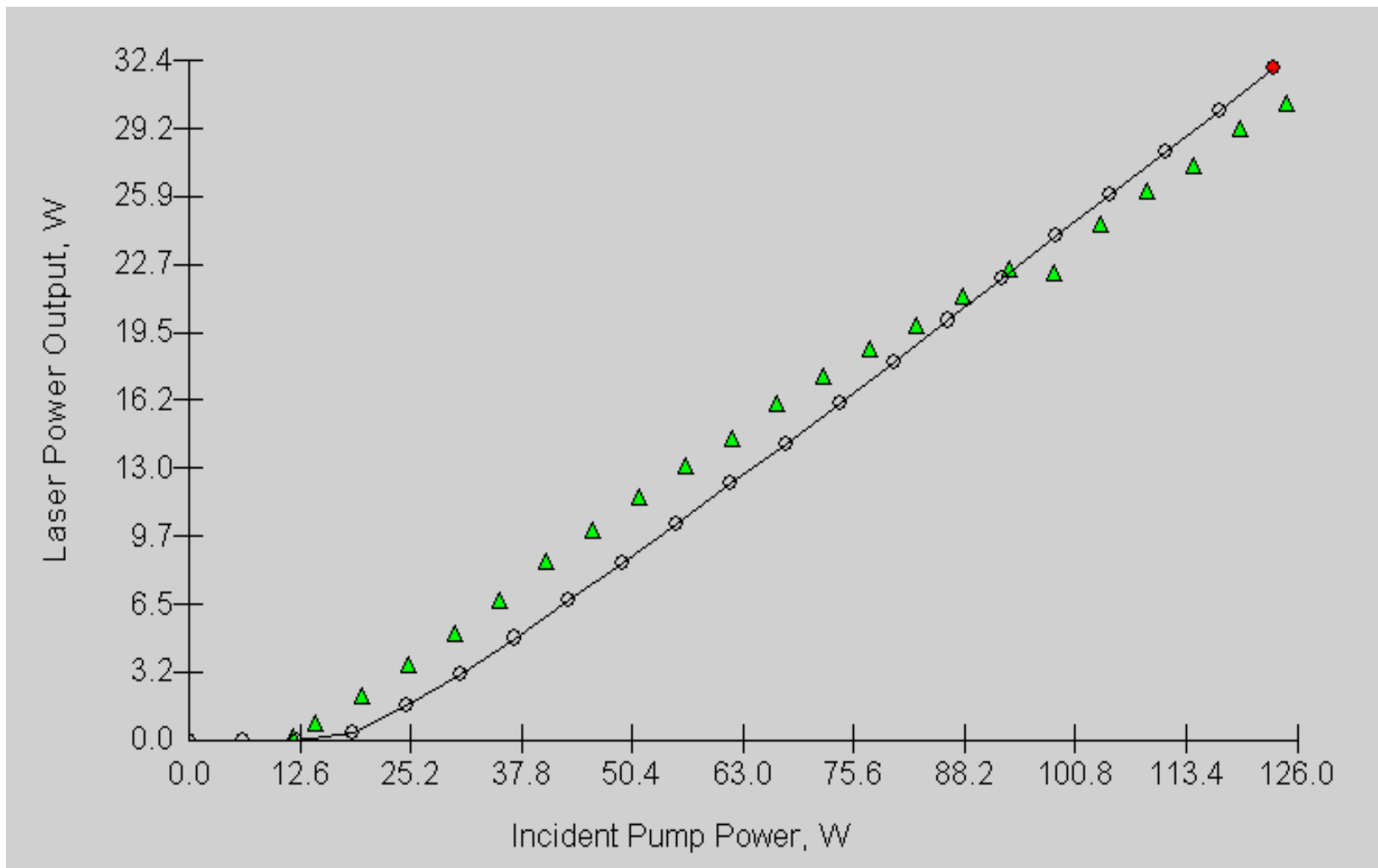
$T(x,y,z)$ [K] is the temperature distribution in the crystal as obtained from FEA.



Energy levels and transitions for the Quasi-3-Level-Material Yb:YAG



Yb:YAG cw-Laser, Laser Group Univ. Kaiserslautern



Output vs. Input Power for a 5 at. % Yb:YAG Laser

- ▲ Measurements: Laser Group Prof. Wallenstein, Univ. Kaiserslautern
- Computation Using Temperature Dependent Stim. Em. Cross Section